

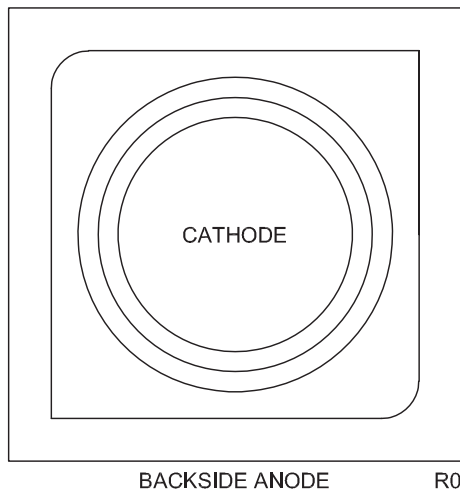
**PROCESS CPZ35R**  
**Transient Voltage Suppressor**  
3.3 Volt TVS Chip



**PROCESS DETAILS**

Die Size	10.2 x 10.2 MILS
Die Thickness	3.9 MILS
Cathode Bonding Pad Area	7.1 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



**GROSS DIE PER 5 INCH WAFER**

163,034

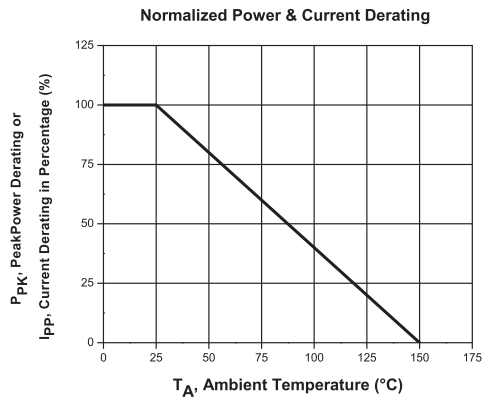
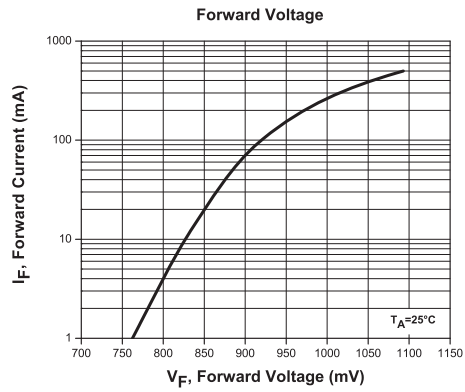
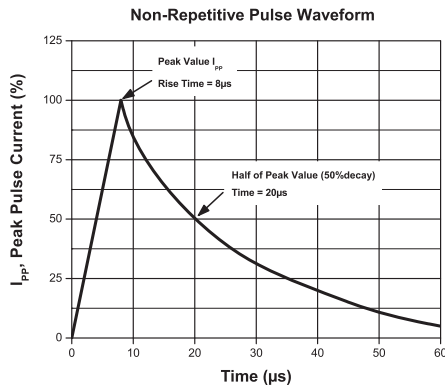
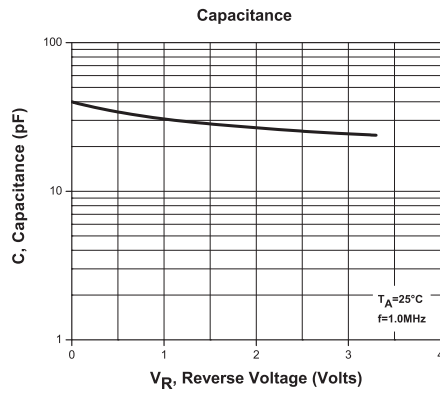
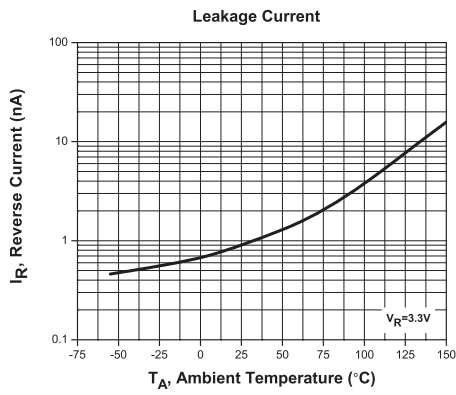
**PRINCIPAL DEVICE TYPE**

CMATVS3V3

R0 (5-January 2012)

# PROCESS CPZ35R

## Typical Electrical Characteristics



R0 (5-January 2012)